TO-263 ṂṂꝈN ઙ ʆ ῷ Ꝣ ꞁ

N-CHANNEL MOSFET in a TO-263 Plastic Package.

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Xowud Orz Rq0Uhvlvwdqfh/idvw vzlwfklqj/ Txdolilhg wr DHF0T434 Vwdqgdugv iru Kljk Uholdelolw|/ KI Surgxfw1

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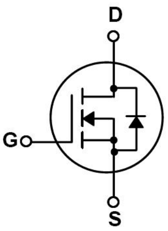
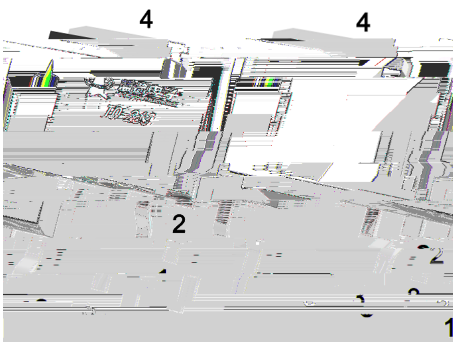
These devices are well suited for high efficient switched mode power supplies Active power factor correction, electronic lamp ballast based on half bridge topology, Meet the stringent requirements of automotive applications.





PIN1 χ G PIN 2 4 χ D PIN 3 χ S

/ Marking

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Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	40	V
Drain Current		I_D(Tc=25)	120	A
Pulsed Drain Current		I_{DM}	480	A
Gate-Source Voltage		V_{GS}	±20	V
Single Pulsed Avalanche Energy		E_{AS}	482	mJ
Avalanche Current		I_{AS}	35	A
Total Power Dissipation		P_D(Tc=25)	187	W
Junction and Storage Temperature Range		T_J,T_{STG}	-55 to 175	
Thermal Resistance-Junction to Ambient	t ≤ 10s	$R_{\theta JA}$	15	/W
	Steady-State		60	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	0.7	

Parameter		Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250 A	40	44		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V V_{GS}=0V			1	
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±1	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250 A	1	1	3	

Static Drain-Source
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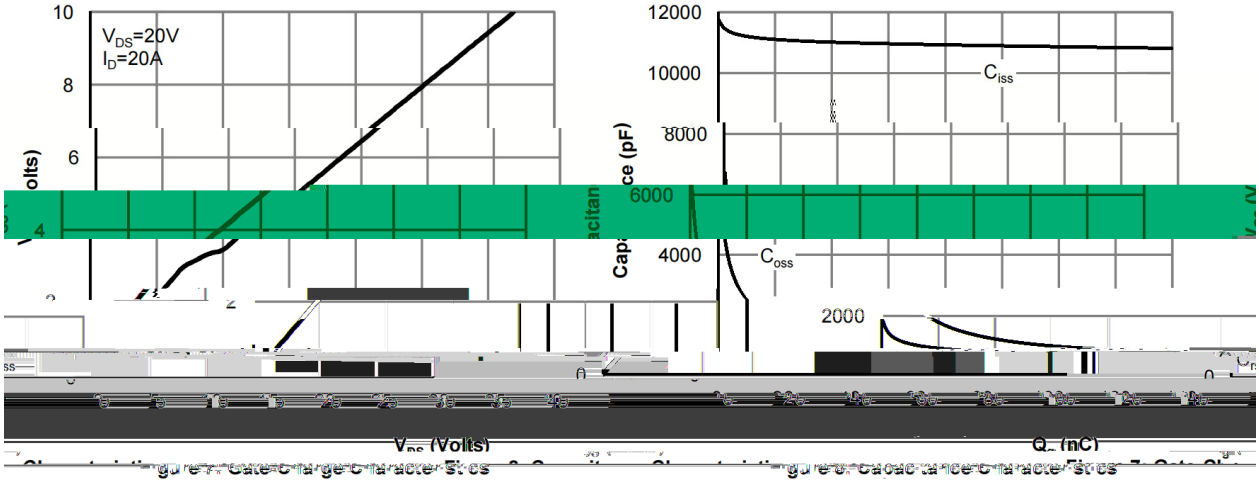
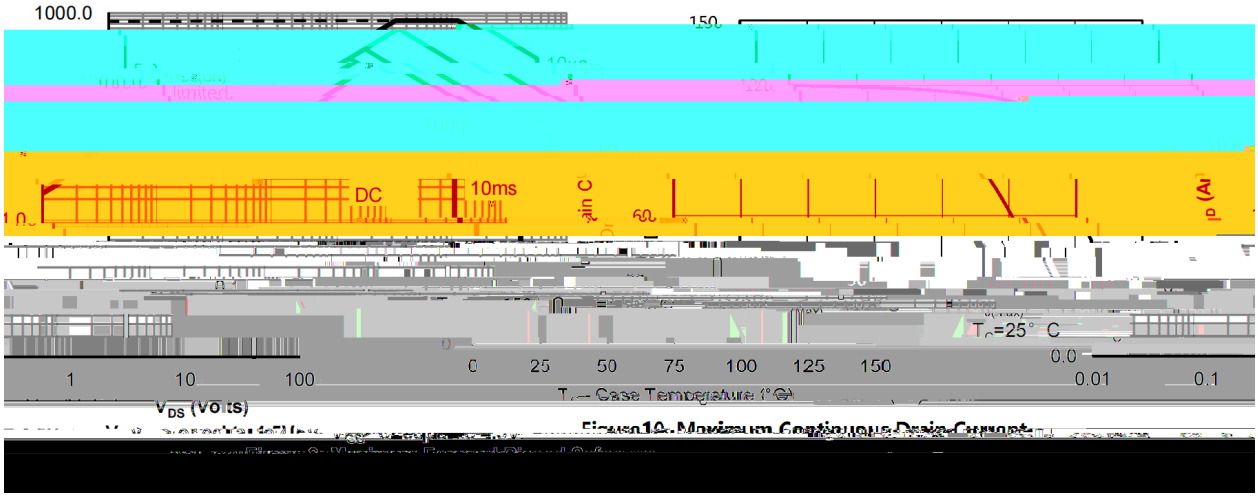
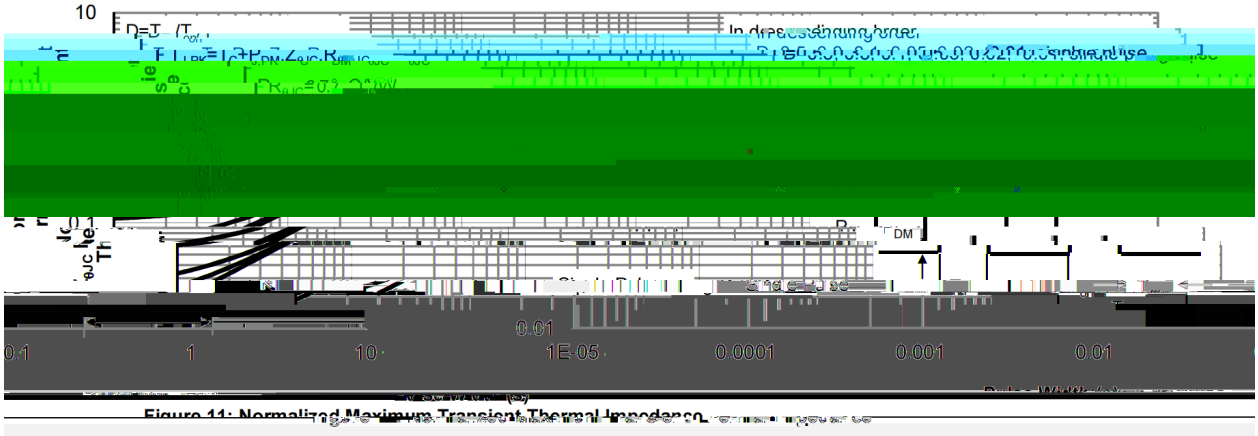
DATA SHEET

/ Electrical Characteristic Curve







/ Package Dimensions